PD-2.325 rev. A 12/97

# MBR735 MBR745

7.5 Amp

# International **tern** Rectifier

## SCHOTTKY RECTIFIER

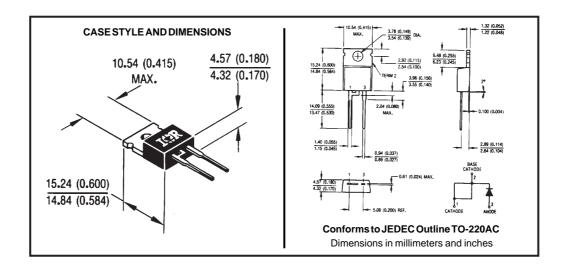
#### **Major Ratings and Characteristics**

Characteristics	MBR7 Unit		
I <sub>F(AV)</sub> Rectangular waveform	7.5	А	
V <sub>RRM</sub>	35/45	V	
I <sub>FSM</sub> @ tp=5µssine	690	А	
V <sub>F</sub> @ 7.5 Apk, T <sub>J</sub> =125°C	0.57	V	
Тј	-65 to 150	°C	

#### **Description/Features**

The MBR7.. Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150° C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- 150° C T operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability



#### MBR735, MBR745

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#### Voltage Ratings

Part number	MBR735	MBR745
V <sub>R</sub> Max. DC Reverse Voltage (V)		
V <sub>RWM</sub> Max. Working Peak Reverse Voltage (V)	35	45

### Absolute Maximum Ratings

	Parameters	MBR7	Units	Conditions
I <sub>F(AV)</sub>	Max.AverageForwardCurrent	7.5	A	@T <sub>c</sub> =120°C,(RatedV <sub>R</sub> )
I <sub>FSM</sub>	Non-RepetitivePeakSurgeCurrent	690	690 A	5µs Sine or 3µs Rect. pulse Following any rated load condition and with rated V <sub>RRM</sub> applied
		150		Surgeappliedatratedloadconditionhalfwavesingle phase60Hz
I <sub>RRM</sub>	PeakRepetitiveReverseSurgeCurrent	1.0	A	2.0 µsec 1.0 KHz

#### **Electrical Specifications**

	Parameters	MBR7	Units	C	Conditions	
V <sub>FM</sub>	Max. Forward Voltage Drop (1)	0.84	V	@ 15A	$T_J = 25 \ ^{\circ}C$	
		0.57	V	@ 7.5A	T 125 %C	
		0.72	V	@ 15A	T <sub>J</sub> = 125 °C	
I <sub>RM</sub>	Max. Instantaneus Reverse Current	0.1	mA	T <sub>J</sub> = 25 °C	Rated DC voltage	
	(1)	15	mA	T <sub>J</sub> = 125 °C	Rated DC voltage	
C <sub>T</sub>	Max. Junction Capacitance	400	pF	$V_R = 5V_{DC}$ , (test signal range 100Khz to 1Mhz) 25°C		
L <sub>S</sub>	Typical Series Inductance	8.0	nH	Measured from top of terminal to mounting plane		
dv/dt	Max. Voltage Rate of Change	1000	V/ µs			
	(Rated V <sub>R</sub> )					

(1) Pulse Width < 300µs, Duty Cycle <2%

### Thermal-Mechanical Specifications

	Parameters		MBR7	Units	Conditions
Т	Max.JunctionTemperatureRa	ange	-65to150	°C	
T <sub>stg</sub>	Max.StorageTemperatureRa	nge	-65to175	°C	
R <sub>thJC</sub>	Max.ThermalResistanceJunt toCase	ction	3.0	°C/W	DCoperation
R <sub>thCS</sub>	TypicalThermalResistance,C toHeatsink	Case	0.50	°C/W	Mountingsurface, smooth and greased
wt	ApproximateWeight		2(0.07)	g(oz.)	
Т	MountingTorque	Min.	6(5)	Kg-cm	
		Max.	12(10)	(Ibf-in)	
	Case Style		TO-220AC		JEDEC

\* For Additional Informations and Graphs, Please See the 6TQ Series